

# AO3415





## **General Description**

The AO3415 uses advanced trench technology to provide excellent R<sub>DS(ON)</sub>, low gate charge and operation with gate voltages as low as 1.8V. This device is suitable for use as a load switch or in PWM applications. It is ESD protected. AO3415 is Pb-free (meets ROHS & Sony 259 specifications). AO3415L is a Green Product ordering option. AO3415 and AO3415L are electrically identical.

### **Features**

 $V_{DS}(V) = -20V$ 

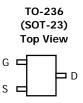
 $I_D = -4 \text{ A } (V_{GS} = -4.5 \text{V})$ 

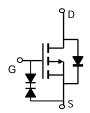
 $R_{DS(ON)} < 43m\Omega \ (V_{GS} = -4.5V)$ 

 $R_{DS(ON)}$  < 54m $\Omega$  (V<sub>GS</sub> = -2.5V)

 $R_{DS(ON)}$  < 73m $\Omega$  ( $V_{GS}$  = -1.8V)

ESD Rating: 3000V HBM





Absolute Maximum Ratings T <sub>A</sub> =25°C unless otherwise noted						
Parameter Drain-Source Voltage Gate-Source Voltage		Symbol	Maximum	Units		
		$V_{DS}$	-20 ±8	V		
		$V_{GS}$				
Continuous Drain	T <sub>A</sub> =25°C		-4.0			
Current <sup>A</sup>	T <sub>A</sub> =70°C	I <sub>D</sub>	-3.5	Α		
Pulsed Drain Current <sup>B</sup>		I <sub>DM</sub>	-30			
	T <sub>A</sub> =25°C	В	1.4	10/		
Power Dissipation <sup>A</sup>	T <sub>A</sub> =70°C	$-P_{D}$	0.9	W		
Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>STG</sub>	-55 to 150	°C		

Thermal Characteristics							
Parameter	Symbol	Тур	Max	Units			
Maximum Junction-to-Ambient A	t ≤ 10s	В	65	90	°C/W		
Maximum Junction-to-Ambient <sup>A</sup>	Steady-State	$ R_{\theta JA}$	85	125	°C/W		
Maximum Junction-to-Lead <sup>C</sup>	Steady-State	$R_{ heta JL}$	43	60	°C/W		

### Electrical Characteristics (T<sub>J</sub>=25°C unless otherwise noted)

Symbol	Parameter	Conditions		Min	Тур	Max	Units
STATIC I	PARAMETERS						
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	$I_D = -250 \mu A, V_{GS} = 0 V$		-20			V
	Zero Gate Voltage Drain Current	V <sub>DS</sub> =-16V, V <sub>GS</sub> =0V				-1	
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	T <sub>J</sub> =55°C				-5	μА
	Gate-Body leakage current	V <sub>DS</sub> =0V, V <sub>GS</sub> =±4.5V				±1	μΑ
I <sub>GSS</sub>	Gate-body leakage current	V <sub>DS</sub> =0V, V <sub>GS</sub> =±8V				±10	μΑ
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS} I_{D}=-250 \mu A$		-0.3	-0.55	-1	
$I_{D(ON)}$	On state drain current	V <sub>GS</sub> =-4.5V, V <sub>DS</sub> =-5V		-25			Α
		$V_{GS}$ =-4.5V, $I_D$ =-4A	_		35	43	mΩ
			T <sub>J</sub> =125°C		48	60	11152
$R_{DS(ON)}$	Static Drain-Source On-Resistance	V <sub>GS</sub> =-2.5V, I <sub>D</sub> =-4A			45	54	mΩ
		V <sub>GS</sub> =-1.8V, I <sub>D</sub> =-2A			56	73	mΩ
	V <sub>GS</sub> =-1.5V, I <sub>D</sub> =-1A				70		mΩ
<b>g</b> FS	Forward Transconductance	V <sub>DS</sub> =-5V, I <sub>D</sub> =-4A		8	16		S
$V_{SD}$	Diode Forward Voltage	I <sub>S</sub> =-1A,V <sub>GS</sub> =0V			-0.78	-1	V
Is	Maximum Body-Diode Continuous Curre	rent				-2.2	Α
DYNAMI	CPARAMETERS						
C <sub>iss</sub>	Input Capacitance	V <sub>GS</sub> =0V, V <sub>DS</sub> =-10V, f=1MHz			1450		pF
C <sub>oss</sub>	Output Capacitance				205		pF
C <sub>rss</sub>	Reverse Transfer Capacitance	7			160		pF
$R_g$	Gate resistance	V <sub>GS</sub> =0V, V <sub>DS</sub> =0V, f=1MHz			6.5		Ω
SWITCHI	NG PARAMETERS		•				
$Q_g$	Total Gate Charge				17.2		nC
$Q_{gs}$	Gate Source Charge	V <sub>GS</sub> =-4.5V, V <sub>DS</sub> =-10V, I <sub>D</sub> =-4A			1.3		nC
$Q_{gd}$	Gate Drain Charge				4.5		nC
t <sub>D(on)</sub>	Turn-On DelayTime				9.5		ns
t <sub>r</sub>	Turn-On Rise Time	$V_{GS}$ =-4.5V, $V_{DS}$ =-10V, $R_L$ =2.5 $\Omega$ , $R_{GEN}$ =3 $\Omega$			17		ns
$t_{D(off)}$	Turn-Off DelayTime				94		ns
t <sub>f</sub>	Turn-Off Fall Time				35		ns
t <sub>rr</sub>	Body Diode Reverse Recovery Time	I <sub>F</sub> =-4A, dI/dt=100A/μs			31		ns
Q <sub>rr</sub>	Body Diode Reverse Recovery Charge	e I <sub>F</sub> =-4A, dI/dt=100A/μs			13.8		nC

A: The value of  $R_{\theta,JA}$  is measured with the device mounted on  $1\text{in}^2$  FR-4 board with 2oz. Copper, in a still air environment with  $T_A$  =25°C. The value in any a given application depends on the user's specific board design. The current rating is based on the  $\bowtie$  10s thermal resistance rating.

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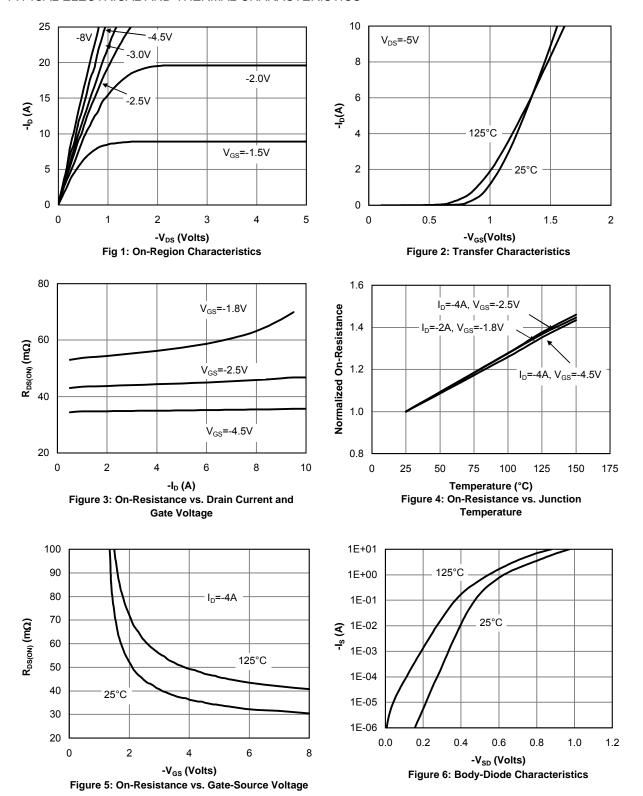
B: Repetitive rating, pulse width limited by junction temperature.

C. The R  $_{\theta JA}$  is the sum of the thermal impedence from junction to lead R $_{\theta JL}$  and lead to ambient.

D. The static characteristics in Figures 1 to 6,12,14 are obtained using  $80\mu s$  pulses, duty cycle 0.5% max.

E. These tests are performed with the device mounted on 1 in  $^2$  FR-4 board with 2oz. Copper, in a still air environment with  $T_A$ =25°C. The SOA curve provides a single pulse rating. Rev 4. September 2005

### TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS



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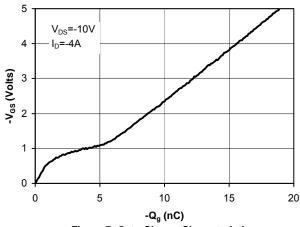


Figure 7: Gate-Charge Characteristics

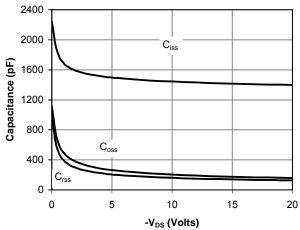


Figure 8: Capacitance Characteristics

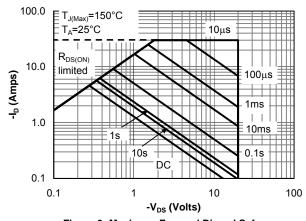


Figure 9: Maximum Forward Biased Safe Operating Area (Note E)

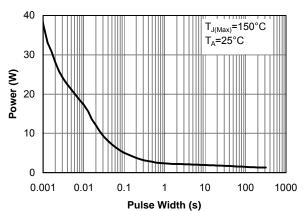


Figure 10: Single Pulse Power Rating Junction-to-Ambient (Note E)

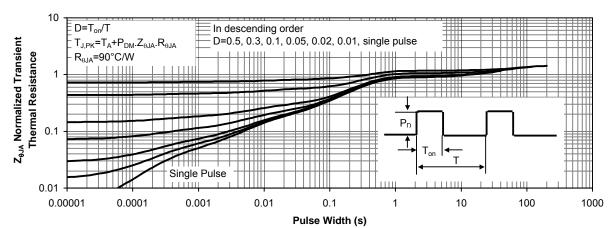
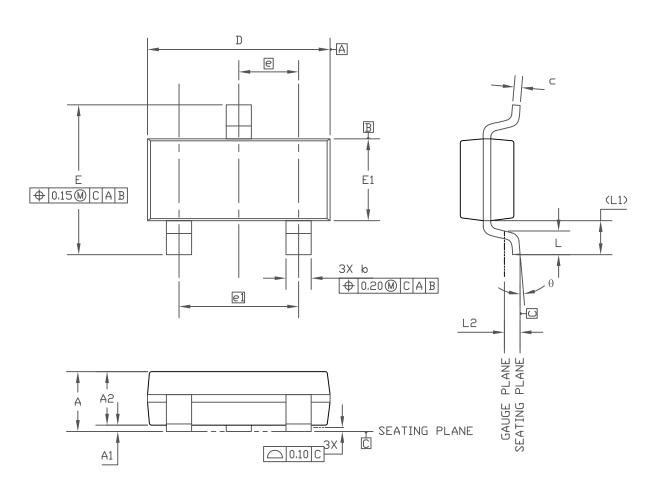


Figure 11: Normalized Maximum Transient Thermal Impedance

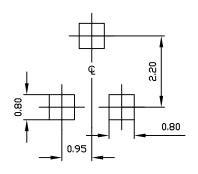


Document No.	PO-00026
Version	rev B

# SOT-23 STANDARD PACKAGE OUTLINE



#### RECOMMENDED LAND PATTERN



UNIT:	mm
01111.	11111

	DIMENSIONS IN MILLIMETERS			DIMENSIONS IN INCHES			
SYMBOLS	MIN	NOM	MAX	MIN	NOM	MAX	
Α	0.75		1.17	0.030		0.046	
A1	0.05		0.15	0.002		0.006	
A2	0.70	0.85	1.02	0.028	0.033	0.040	
b	0.30		0.50	0.012		0.020	
С	0.08		0.20	0.003		0.008	
D	2.80	2.90	3.04	0.110	0.114	0.120	
Е	2.10		2.64	0.083		0.104	
E1	1.20	1.30	1.40	0.047	0.051	0.055	
e	0.95 BSC			0.037 BSC			
e1	1.90 BSC			0.075 BSC			
L	0.40	0.50	0.60	0.016	0.020	0.024	
L1	0.54 REF			0.021REF			
L2	0.25			0.010			
θ1	00		80	00		80	

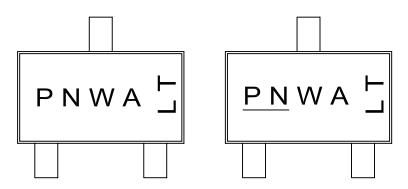
#### NOTE

- 1. ALL DIMENSIONS ARE IN MILLIMETERS.
- 2. CONTROLLING DIMENSION IS MILLIMETER. CONVERTED INCH DIMENSIONS ARE NOT NECESSARILY EXACT.
- 3. DIMENSION D DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH, PROTRUSIONS OR GATE BURRS SHALL NOT EXCEED 0.25 mm PER END. DIMENSION E1 DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 mm PER SIDE.
- 4. THE PACKAGE TOP MAY BE SMALLER THAN THE PACKAGE BOTTOM. DIMENSIONS D AND E1 ARE DETERMINED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY EXCLUSIVE OF MOLD FLASH, TIE BAR BURRS, GATE BURRS AND INTERLEAD FLASH, BUT INCLUDING ANY MISMATCH BETWEEN THE TOP AND BOTTOM OF THE PLASTIC BODY.
- 5. FOLLOW JEDEC TO-236H AA.



Document No.	PD-00120	
Version	D	
Title	AO3415 Marking Description	

### SOT-23 PACKAGE MARKING DESCRIPTION



Standard product

Green product

### NOTE:

P - Package and product type

N - Last digital of product number

W - Year and week code

A - Assembly location code

L&T - Assembly lot code

PART NO.	DESCRIPTION	CODE (PN)
AO3415	Standard product	AF
AO3415L	Green product	<u>AF</u>

